


ESA-QCA9967T-C

	TOTAL DOSE RADIATION TEST REPORT No. HUY-RR-TL-004	Issue: 1 Rev.: Date: 29/07/94 Page: 1/81
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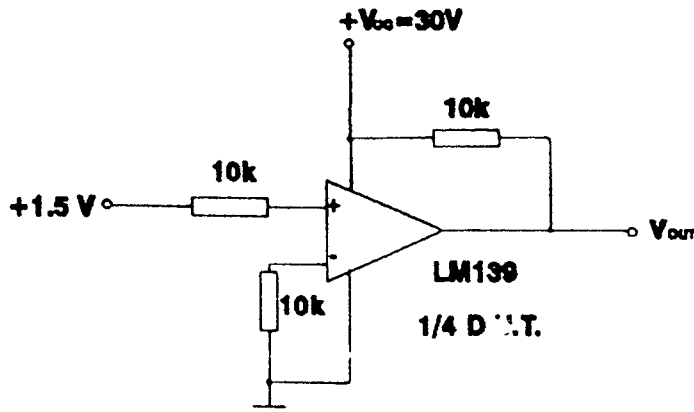
SCC Component No.: 910300404B	Component Designation: LM139AJ	Irradiation Spec. No.: ESA/SCC 22900-Iss.2
Gen. Spec.: SCC9000 8 Det. Spec.: SCC9103/004 1C Amend.:	Evaluation: - Acceptance Diffusion: - Acceptance Lot: X	Project/Programme: HUYGENS File: 10 APR 1996
Family: 08 Group: 06	Functional Assignment: QUAD COMPARATOR	Package: MS2008 ESTEC SN: 44574
Manuf. Name: MOTOROLA Address: TOULOUSE (FRANCE)	Irradiation Facility: CIEMAT Address: MADRID (SPAIN)	Test House: TECNOLOGICA Address: SEVILLA (SPAIN)
Radiation Test Plan No.: HUY-IP-TL-004 Iss.3	Sample Size: 5 Irradiation Devices: 4 Control Devices: 1	Date Code: 9320 Diffusion LOT: 45301 Wafer N°: 13
Radiation Source: Cobalt-60	Energy: 1,33 / 1,17 MeV Dose Rate: 20 kRad/h	Date of Test: 06/94

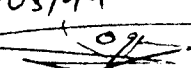


Electrical Measurements. Parameters Tested:

Input Offset Voltage (V_{i01} , V_{i02} , V_{i03} & V_{i04}), Input Bias Current (I_{i1+} , I_{i2+} , I_{i3+} & I_{i4+}), Input Bias Current (I_{i1-} , I_{i2-} , I_{i3-} & I_{i4-}), Input Offset Current (I_{o1} , I_{o2} , I_{o3} & I_{o4}), Open Loop Gain (A_{v1}) and Common Mode Rejection Ratio (CMRR1 & CMRR2).

Irradiation Conditions: Biased: Y Test Circuit: Figure 1	Irradiation Measurements Interval: Biased: N Test Circuit: N/A	Annealing Tests: YES Biased: Y Time: 24/168h Temp.: 25°C Test Circuit: Figure 1
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Figure 1:



Irradiat. Respons.: J.A. VAQUERO Date: 01/08/94 Signature: 	Electr. Test Resp.: J.M. VALLEKDE Date: 02/09/94 Signature: 	Approved by QA: L. DE PABLO Date: 9.09.94 Signature: 
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	00 KRAD	10 KRAD	15 KRAD	20 KRAD	30 KRAD	50 KRAD	ANN24	ANN168
IB1+1	PASS	6 PASS 10 FAIL	FAIL	FAIL	FAIL	FAIL	FAIL	FAIL
IB1+2	PASS	PASS	2 PASS 14 FAIL	FAIL	FAIL	FAIL	FAIL	FAIL
IB1+3	PASS	8 PASS 8 FAIL	FAIL	FAIL	FAIL	FAIL	FAIL	FAIL
IB1+4	PASS	12 PASS 4 FAIL	FAIL	FAIL	FAIL	FAIL	FAIL	FAIL
AVS	PASS	PASS	PASS	PASS	PASS	FAIL	FAIL	PASS
CMRR1	PASS	PASS	PASS	PASS	PASS	PASS	10 PASS 6 FAIL	7 PASS 9 FAIL
CMRR2	PASS	PASS	PASS	PASS	PASS	PASS	PASS	16 PASS 1 FAIL

CONCLUSION

The results indicates that:

- All comparators fail in input offset voltage measurements (VIO1, VIO2, VIO3 & VIO4) between 10 and 50 KRads and the measurements get worse during the annealing.
- All comparators fail in input offset current measurements (IIO1, IIO2, IIO3 & IIO4) between 20 and 50 KRads and the measurements get worse during the annealing.
- Input bias currents measurements (IB+1, IB+2, IB+3, IB+4, IB-1, IB-2, IB-3, IB-4) fails beetween 10 and 15 Krads and recover slightly during annealing.
- Open loop gain measurements fail at 30 Krads in all comparators but it recovers under spec after annealing 168h.
- CMRR measurements remains under specs during the irradiation exposure but some comparators fail during annealing.



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Test Step	Description	Result or Actual Test Condition	Time in	Time Out	Exposure
1	Sample serialization	CONTROL R1,R2,R3,R4,R5.			
2	Initial Electrical Measurements	See 0 krad(Si) values in respective Parameter Data Tables	10:05 16/06	10:35 16/06	
3	Set-up of Test	Bias circuit verified according to Fig. 1			
4	Irradiation Exposure	Cumulative Dose: 10 krad(Si) Dose Rate: 20 kRad(Si)/h Temperature: 20.2 °C	10:35	11:05	30 min.
5	Intermediate Electrical Measurements	See 10 krad(Si) values in respective Parameter Data Tables	11:05	11:23	
6	Set-up of Test	Bias circuit verified according to Fig. 1			
7	Irradiation Exposure	Cumulative Dose: 15 krad(Si) Dose Rate: 20 kRad(Si)/h Temperature: 21.4 °C	11:23	11:38	15 min.
8	Intermediate Electrical Measurements	See 15 krad(Si) values in respective Parameter Data Tables	11:38	12:06	
9	Set-up of Test	Bias circuit verified according to Fig. 1			
10	Irradiation Exposure	Cumulative Dose: 20 krad(Si) Dose Rate: 20 kRad(Si)/h Temperature: 22.4 °C	12:06	12:21	15 min.
11	Intermediate Electrical Measurements	See 20 krad(Si) values in respective Parameter Data Tables	12:21	12:29	
12	Set-up of Test	Bias circuit verified according to Fig. 1			
13	Irradiation Exposure	Cumulative Dose: 30krad(Si) Dose Rate: 20 kRad(Si)/h Temperature: 22.7 °C	12:29	12:59	30 min.



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Test Step	Description	Result or Actual Test Condition	Time in	Time Out	Exposure
14	Intermediate Electrical Measurements	See 30 krad(Si) values in respective Parameter Data Tables	12:59	13:22	
15	Set-up of Test	Bias circuit verified according to Fig. 1			
16	Irradiation Exposure	Cumulative Dose: 50krad(Si) Dose Rate: 20 kRad(Si)/h Temperature: 23.5 °C	13:22	14:22	60 min.
17	Intermediate Electrical Measurements	See 50 krad(Si) values in respective Parameter Data Tables	14:22	14:37	
18	Annealing	Bias circuit verified according to Fig. 1. Temperature: 22.5 °C (average)	14:37 16/06	14:37 27/06	24 h
19	Electrical Measurements	See 24 h values in respective Parameter Data Tables	14:37	14:53	
20	Annealing	Bias circuit verified according to Fig. 1. Temperature: 22.8 °C (average)	14:53 17/01	14:53 24/01	168 h
21	Electrical Measurements	See 168 h values in respective Parameter Data Tables	14:53	15:06	

